

IEEE HOME | SEARCH IEEE | SHOP | WEB ACCOUNT | CONTACT IEEE

Membership Publications/Services Standards Conferences Careers/Jobs

IEEE Xplore™
RELEASE 1.4

Welcome
United States Patent and Trademark Office

Help FAQ Terms IEEE Peer Quick Links

Review

Welcome to IEEE Xplore™

- ☐ Home
- ☐ What Can I Access?
- ☐ Log-out

Tables of Contents

- ☐ Journals & Magazines
- ☐ Conference Proceedings
- ☐ Standards

Search

- ☐ By Author
- ☐ Basic
- ☐ Advanced

Member Services

- ☐ Join IEEE
- ☐ Establish IEEE Web Account

 Print FormatYour search matched **1358** of **767657** documents.Results are shown **25** to a page, sorted by **publication year** in **descending** order.

You may refine your search by editing the current search expression or entering a new one the text

Then click **Search Again**.**Results:**Journal or Magazine = **JNL** Conference = **CNF** Standard = **STD****1 Has SiGe lowered the noise in transistors?***Chroboczek, J.A.; Ghibaudo, G.*Circuits, Devices and Systems, IEE Proceedings- , Volume: 149 Issue: 1 , Feb. 2
Page(s): 51 -58[\[Abstract\]](#) [\[PDF Full-Text \(915 KB\)\]](#) **JNL****2 A high-power and high-gain X-band Si/SiGe/Si heterojunction bipolar transistor***Zhenqiang Ma; Mohammadi, S.; Bhattacharya, P.; Katehi, L.P.B.; Alterovitz, S. Ponchak, G.E.*Microwave Theory and Techniques, IEEE Transactions on , Volume: 50 Issue: 4
2002

Page(s): 1101 -1108

[\[Abstract\]](#) [\[PDF Full-Text \(329 KB\)\]](#) **JNL****3 The correlation resistance for low-frequency noise compact modeling Si/SiGe HBTs***Borgarino, M.; Bary, L.; Vescovi, D.; Menozzi, R.; Monroy, A.; Laurens, M.; Plan Fantini, F.; Graffeuil, J.*Electron Devices, IEEE Transactions on , Volume: 49 Issue: 5 , May 2002
Page(s): 863 -870[\[Abstract\]](#) [\[PDF Full-Text \(333 KB\)\]](#) **JNL****4 Simulation of quantum effects along the channel of ultrascaled Si-bas MOSFETs**

Wanqiang Chen; Register, L.F.; Banerjee, S.K.

Electron Devices, IEEE Transactions on , Volume: 49 Issue: 4 , April 2002

Page(s): 652 -657

[\[Abstract\]](#) [\[PDF Full-Text \(290 KB\)\]](#) [JNL](#)

5 Self-aligned sige npn transistors with 285 GHz $f_{\text{sub MAX}}$ and 207 G $f_{\text{sub T}}$ in a manufacturable technology

Jagannathan, B.; Khater, M.; Pagette, F.; Rieh, J.-S.; Angell, D.; Chen, H.; Flor Golan, F.; Greenberg, D.R.; Groves, R.; Jeng, S.J.; Johnson, J.; Mengistu, E.; Schonenberg, K.T.; Schnabel, C.M.; Smith, P.; Stricker, A.; Ahlgren, D.; Freeman

IEEE Electron Device Letters , Volume: 23 Issue: 5 , May 2002

Page(s): 258 -260

[\[Abstract\]](#) [\[PDF Full-Text \(232 KB\)\]](#) [JNL](#)

6 Minimizing thermal resistance and collector-to-substrate capacitance BiCMOS on SOI

Mastrapasqua, M.; Palestri, P.; Pacelli, A.; Celler, G.K.; Frei, M.R.; Smith, P.R.; Johnson, R.W.; Bizzarro, L.; Lin, W.; Ivanov, T.G.; Carroll, M.S.; Kizilyalli, I.C.; C.A.

IEEE Electron Device Letters , Volume: 23 Issue: 3 , March 2002

Page(s): 145 -147

[\[Abstract\]](#) [\[PDF Full-Text \(193 KB\)\]](#) [JNL](#)

7 Technological requirements for a lateral SiGe HBT technology including theoretical performance predictions relative to vertical SiGe HBTs

Hamel, J.S.; Tang, Y.T.; Osman, K.

Electron Devices, IEEE Transactions on , Volume: 49 Issue: 3 , March 2002

Page(s): 449 -456

[\[Abstract\]](#) [\[PDF Full-Text \(193 KB\)\]](#) [JNL](#)

8 The effects of geometrical scaling on the frequency response and n is performance of SiGe HBTs

Shiming Zhang; Guofu Niu; Cressler, J.D.; Joseph, A.J.; Freeman, G.; Hamee,

Electron Devices, IEEE Transactions on , Volume: 49 Issue: 3 , March 2002

Page(s): 429 -435

[\[Abstract\]](#) [\[PDF Full-Text \(214 KB\)\]](#) [JNL](#)

9 Improving contact performances of Al(Al/Pd) and i-a-SiGe:H interface an additional very thin Sb layer

Cha-Shin Lin; Rong-Hwei Yeh; Inn-Xin Li; Jyh-Wong Hong
Electronics Letters , Volume: 38 Issue: 5 , 28 Feb. 2002
Page(s): 253 -255

[\[Abstract\]](#) [\[PDF Full-Text \(437 KB\)\]](#) [JNL](#)

10 Hole velocity overshoot in partially strain compensated Si/sub 0.793/Ge/sub 0.2/C/sub 0.007/ inversion layers [MOSFETs]
Kar, G.S.; Maikap, S.; Banerjee, S.K.; Ray, S.K.
Electronics Letters , Volume: 38 Issue: 3 , 31 Jan. 2002
Page(s): 141 -142

[\[Abstract\]](#) [\[PDF Full-Text \(213 KB\)\]](#) [JNL](#)

11 Compound interest
Snowden, C.M.
IEE Review , Volume: 48 Issue: 1 , Jan. 2002
Page(s): 15 -20

[\[Abstract\]](#) [\[PDF Full-Text \(306 KB\)\]](#) [JNL](#)

12 47 GHz VCO with low phase noise fabricated in a SiGe bipolar pr duc technology
Li, H.; Rein, H.-M.; Kreienkamp, R.; Klein, W.
Microwave and Wireless Components Letters, IEEE , Volume: 12 Issue: 3 , Marc
Page(s): 79 -81

[\[Abstract\]](#) [\[PDF Full-Text \(252 KB\)\]](#) [JNL](#)

13 Ge-profile design for improved linearity of SiGe double HBTs
Gunnar Malm, B.; Ostling, M.
IEEE Electron Device Letters , Volume: 23 Issue: 1 , Jan. 2002
Page(s): 19 -21

[\[Abstract\]](#) [\[PDF Full-Text \(54 KB\)\]](#) [JNL](#)

14 Reflection-type optical waveguide switch with bow-tie electrode
Baojun Li; Soo-Jin Chua
Lightwave Technology, Journal of , Volume: 20 Issue: 1 , Jan. 2002
Page(s): 65 -70

[\[Abstract\]](#) [\[PDF Full-Text \(116 KB\)\]](#) [JNL](#)

15 RF-S C-expectations and required conditions*Matsuzawa, A.*Microwave Theory and Techniques, IEEE Transactions on , Volume: 50 Issue: 1
Jan. 2002

Page(s): 245 -253

[\[Abstract\]](#) [\[PDF Full-Text \(402 KB\)\]](#) [JNL](#)**16 The silicon radio decade***Sevenhans, J.; Op't Eynde, F.; Reusens, P.*Microwave Theory and Techniques, IEEE Transactions on , Volume: 50 Issue: 1
Jan. 2002

Page(s): 235 -244

[\[Abstract\]](#) [\[PDF Full-Text \(156 KB\)\]](#) [JNL](#)**17 A completely integrated 1.9-GHz receiver front-end with monolithic image-reject filter and VCO***Rogers, J.W.M.; Macedo, J.A.; Plett, C.*Microwave Theory and Techniques, IEEE Transactions on , Volume: 50 Issue: 1
Jan. 2002

Page(s): 210 -215

[\[Abstract\]](#) [\[PDF Full-Text \(314 KB\)\]](#) [JNL](#)**18 A 0.2-/spl mu/m 180-GHz-f/sub max/ 6.7-ps-ECL SOI/HRS self-align SEG SiGe HBT/CMOS technology for microwave and high-speed digital applications***Washio, K.; Ohue, E.; Shimamoto, H.; Oda, K.; Hayami, R.; Kiyota, Y.; Tanabe Kondo, M.; Hashimoto, T.; Harada, T.*

Electron Devices, IEEE Transactions on , Volume: 49 Issue: 2 , Feb. 2002

Page(s): 271 -278

[\[Abstract\]](#) [\[PDF Full-Text \(186 KB\)\]](#) [JNL](#)**19 Novel SOI p-channel MOSFETs with higher strain in si channel using SiGe heterostructures***Mizuno, T.; Sugiyama, N.; Tezuka, T.; Takagi, S.*

Electron Devices, IEEE Transactions on , Volume: 49 Issue: 1 , Jan. 2002

Page(s): 7 -14

[\[Abstract\]](#) [\[PDF Full-Text \(211 KB\)\]](#) [JNL](#)

20 Design and fabrication of 50-nm thin-body p-MOSFETs with a SiGe heterostructure channel

Yee-Chia Yeo; Subramanian, V.; Kedzierski, J.; Peiqi Xuan; Tsu-Jae King; Bokor Chenming Hu

Electron Devices, IEEE Transactions on, Volume: 49 Issue: 2, Feb. 2002

Page(s): 279 -286

[\[Abstract\]](#) [\[PDF Full-Text \(194 KB\)\]](#) [JNL](#)

21 A 10-GHz SiGe BiCMOS phase-locked-loop frequency synthesizer

Klepser, B.-U.H.; Scholz, M.; Gotz, E.

Solid-State Circuits, IEEE Journal of, Volume: 37 Issue: 3, March 2002

Page(s): 328 -335

[\[Abstract\]](#) [\[PDF Full-Text \(167 KB\)\]](#) [JNL](#)

22 A 32-word by 32-bit three-port bipolar register file implemented using SiGe HBT BiCMOS technology

Steidl, S.A.; McDonald, J.F.

Solid-State Circuits, IEEE Journal of, Volume: 37 Issue: 2, Feb. 2002

Page(s): 228 -236

[\[Abstract\]](#) [\[PDF Full-Text \(165 KB\)\]](#) [JNL](#)

23 50Gb/s SiGe BiCMOS 4:1 multiplexer and 1:4 demultiplexer for serial communication systems

Meghelli, M.; Rylyakov, A.V.; Lei Shan

Solid-State Circuits Conference, 2002. Digest of Technical Papers. 2002 IEEE International, Volume: 1, 2002

Page(s): 260 -465

[\[Abstract\]](#) [\[PDF Full-Text \(445 KB\)\]](#) [CNF](#)

24 A highly-integrated tri-band/quad-mode SiGe BiCMOS RF-to-baseband receiver for wireless CDMA/WCDMA/AMPS applications with GPS capability

Aparin, V.; Gazzerro, P.; Jianjun Zhou; Bo Sun; Szabo, S.; Zeisel, E.; Segoria, Ciccirelli, S.; Persico, C.; Narathong, C.; Sridhara, R.

Solid-State Circuits Conference, 2002. Digest of Technical Papers. 2002 IEEE International, Volume: 1, 2002

Page(s): 234 -235

[\[Abstract\]](#) [\[PDF Full-Text \(390 KB\)\]](#) [CNF](#)

25 A highly-integrated SiGe BiCMOS WCDMA transmitter IC

Bellaouar, A.; Frechette, M.; Fridi, A.R.; Embabi, S.H.K.

Solid-State Circuits Conference, 2002. Digest of Technical Papers. 2002 IEEE International , Volume: 1 , 2002

Page(s): 238 -463

[\[Abstract\]](#) [\[PDF Full-Text \(372 KB\)\]](#) **CNF**

[1](#) [2](#) [3](#) [4](#) [5](#) [6](#) [7](#) [8](#) [9](#) [10](#) [11](#) [12](#) [13](#) [14](#) [15](#) [16](#) [17](#) [18](#) [19](#) [20](#) [21](#) [22](#) [23](#) [24](#) [25](#) [26](#) [27](#) [28](#) [29](#)

[33](#) [34](#) [35](#) [36](#) [37](#) [38](#) [39](#) [40](#) [\[Next\]](#)

[Home](#) | [Log-out](#) | [Journals](#) | [Conference Proceedings](#) | [Standards](#) | [Search by Author](#) | [Basic Search](#) | [Advanced Search](#)
[Join IEEE](#) | [Web Account](#) | [New this week](#) | [OPAC Linking Information](#) | [Your Feedback](#) | [Technical Support](#) | [Email Alerting](#)
[No Robots Please](#) | [Release Notes](#) | [IEEE Online Publications](#) | [Help](#) | [FAQ](#) | [Terms](#) | [Back to Top](#)

Copyright © 2002 IEEE — All rights reserved

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	2	257/577.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:30
2	BRS	L2	13	257/586.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:31
3	BRS	L3	10	257/431.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:32
4	BRS	L4	7	257/15.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:33
5	BRS	L5	42	257/19.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:54
6	BRS	L6	38	257/21.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
7	BRS	L7	30	257/22.ccls. and sige	USPAT; EPO; JPO; DERWEN T; IBM_TD B	2002/05/23 08:56